DSA7003

Silicon PNP epitaxial planar type

For low frequency output amplification Complementary to DSC7003

Features

- \bullet Low collector-emitter saturation voltage $V_{\mbox{CE(sat)}}$
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 1000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-60	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Emitter-base voltage (Collector open)	V _{EBO}	-5	V
Collector current	I _C	-1	А
Peak collector current	I _{CP}	-1.5	А
Collector power dissipation *	P _C	1	W
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Package

- Code
- MiniP3-F2-B
- Pin Name
 - 1. Base
 - 2. Collector
 - 3. Emitter
- Marking Symbol: 4A

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

Absolute maximum rating without heat sink for P_C is 0.5 W

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{\rm CE} = -10$ V, $I_{\rm C} = -500$ mA	120		340	
	h _{FE2}	$V_{CE} = -5 V, I_C = -1 A$	50			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = -500 \text{ mA}, I_{\rm B} = -50 \text{ mA}$			- 0.4	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_{\rm C} = -500 \text{ mA}, I_{\rm B} = -50 \text{ mA}$			-1.2	V
Transition frequency	f _T	$V_{\rm CE} = -10$ V, $I_{\rm C} = -50$ mA		120		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		14.5	30	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

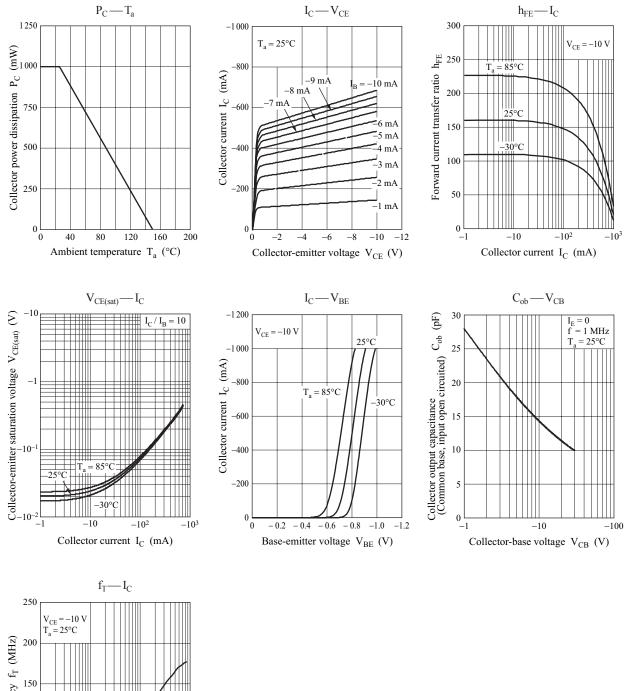
*2: Rank classification

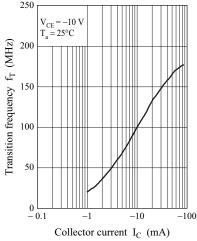
Code	R	S	0		
Rank	R	S	No-rank		
h _{FE1}	120 to 240	170 to 340	120 to 340		
Marking Symbol	4AR	4AS	4A		

Product of no-rank is not classified and have no marking symbol for rank.

DSA7003

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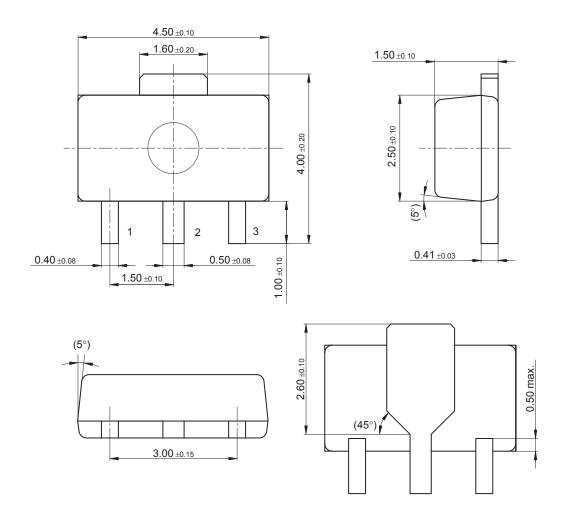




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MiniP3-F2-B

Unit: mm



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